



**6N65-CBS**

Preliminary

*Power MOSFET*

**6.0A, 650V N-CHANNEL  
POWER MOSFET**

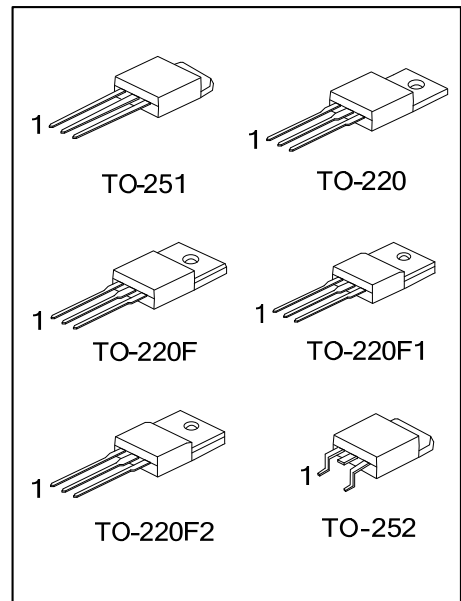
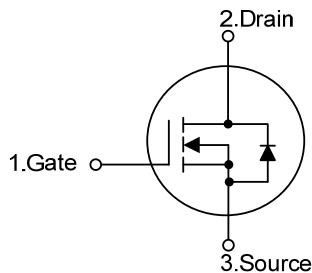
■ DESCRIPTION

The UTC **6N65-CBS** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in switching power supplies and adaptors.

■ FEATURES

- \*  $R_{DS(ON)} < 1.8\Omega @ V_{GS} = 10V, I_D = 3.0A$
- \* Fast switching capability
- \* Avalanche energy tested
- \* Improved dv/dt capability, high ruggedness

■ SYMBOL



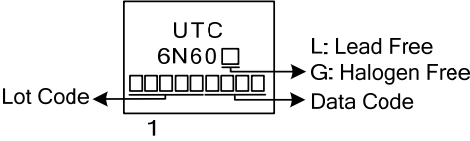
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
6N65L-TA3-T	6N65G-TA3-T	TO-220	G	D	S	Tube
6N65L-TF1-T	6N65G-TF1-T	TO-220F1	G	D	S	Tube
6N65L-TF2-T	6N65G-TF2-T	TO-220F2	G	D	S	Tube
6N65L-TF3-T	6N65G-TF3-T	TO-220F	G	D	S	Tube
6N65L-TM3-R	6N65G-TM3-R	TO-251	G	D	S	Tape Reel
6N65L-TN3-R	6N65G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>6N60L-TA3-T</p>	<p>(1) T: Tube, R: Tape Reel                  (2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TM3: TO-251, TN3: TO-252                  (3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING



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■ ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	650	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Drain Current	Continuous	$I_D$	6	A
	Pulsed (Note 2)	$I_{DM}$	24	A
Avalanche Current (Note 2)		$I_{AR}$	2.5	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	31	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.2	V/ns
Power Dissipation	TO-220	$P_D$	125	W
	TO-220F/TO-220F1		40	W
	TO-220F2		42	
	TO-251/TO-252		55	W
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3.  $L = 10\text{mH}$ ,  $I_{AS} = 2.5\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$

4.  $I_{SD} \leq 6.0\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	PACKAGE	SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F	$\theta_{JA}$	62.5	$^\circ\text{C}/\text{W}$
	TO-220F1/TO-220F2			
	TO-251/TO-252			
Junction to Case	TO-220	$\theta_{JC}$	1.0	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		3.2	$^\circ\text{C}/\text{W}$
	TO-220F2		2.97	$^\circ\text{C}/\text{W}$
	TO-251/TO-252		2.27	$^\circ\text{C}/\text{W}$

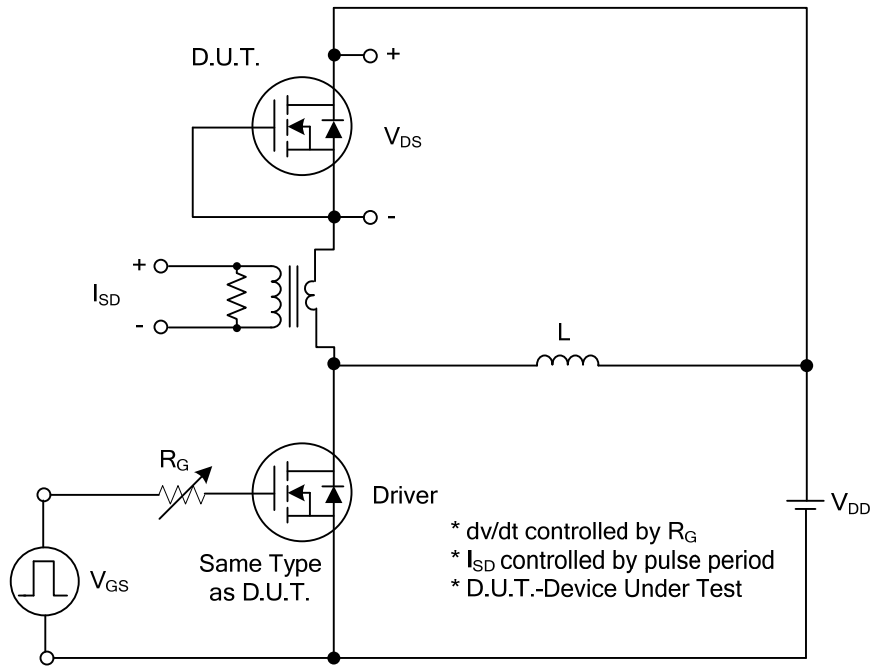
■ ELECTRICAL CHARACTERISTICS ( $T_J=25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	650			V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=650V, V_{GS}=0V$			10	$\mu A$
Gate- Source Leakage Current	Forward	$V_G=30V, V_{DS}=0V$ $V_{GS}=-30V, V_{DS}=0V$			100	nA
	Reverse				-100	nA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=3.0A$			1.8	$\Omega$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{ISS}$	$V_{GS}=0V, V_{DS}=25V, f=1.0\text{ MHz}$		920		pF
Output Capacitance	$C_{OSS}$			75		pF
Reverse Transfer Capacitance	$C_{RSS}$			60		pF
<b>SWITCHING CHARACTERISTICS</b>						
Total Gate Charge (Note 1)	$Q_G$	$V_{DS}=50V, V_{GS}=10V, I_D=1.3A$ $I_G=100\mu A$ (Note 1, 2)		23		nC
Gate to Source Charge	$Q_{GS}$			4		nC
Gate to Drain Charge	$Q_{GD}$			3.8		nC
Turn-ON Delay Time (Note 1)	$t_{D(ON)}$	$V_{DD}=30V, V_{GS}=10V, I_D=0.5A$ $R_G=25\Omega$ (Note 1, 2)		55		ns
Rise Time	$t_R$			28		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			165		ns
Fall-Time	$t_F$			30		ns
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
Maximum Body-Diode Continuous Current	$I_S$				6	A
Maximum Body-Diode Pulsed Current	$I_{SM}$				24	A
Drain-Source Diode Forward Voltage (Note 1)	$V_{SD}$	$I_S=6.0A, V_{GS}=0V$			1.4	V
Body Diode Reverse Recovery Time (Note 1)	$t_{rr}$	$I_S=6.0A, V_{GS}=0V$ $di_f/dt=100A/\mu s$ (Note 1)		460		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			2.2		$\mu C$

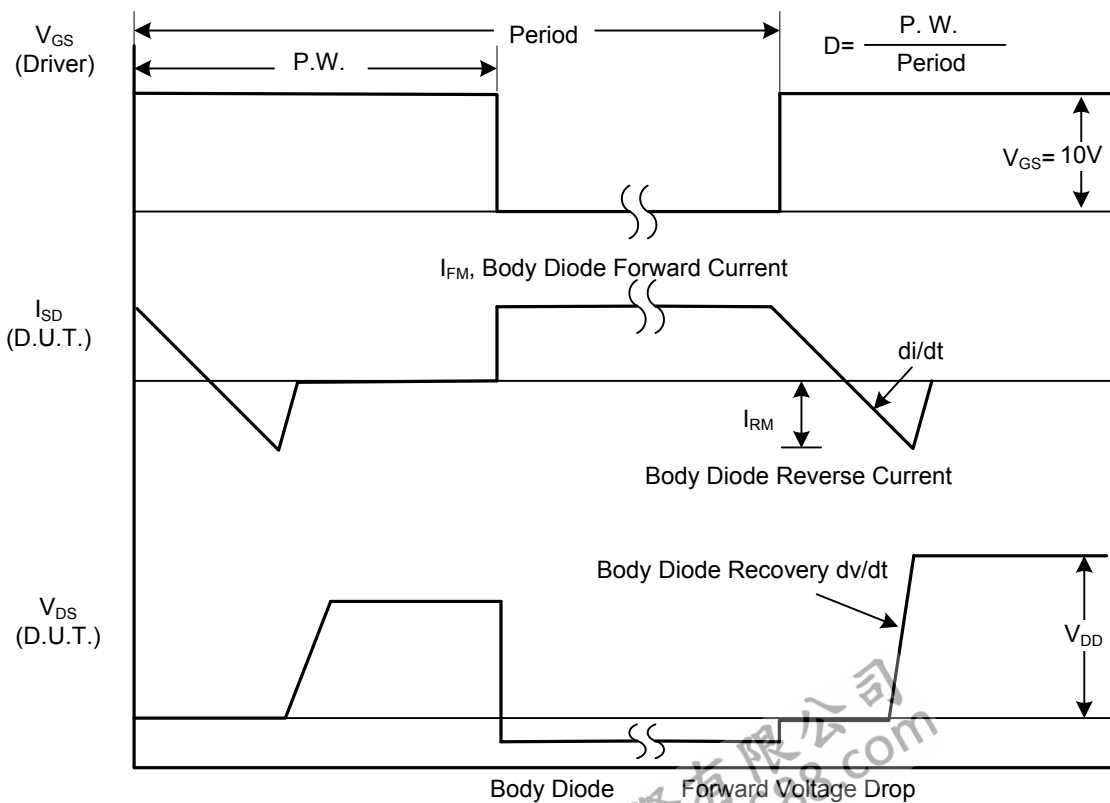
Notes: 1. Pulse Test: Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$ .

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

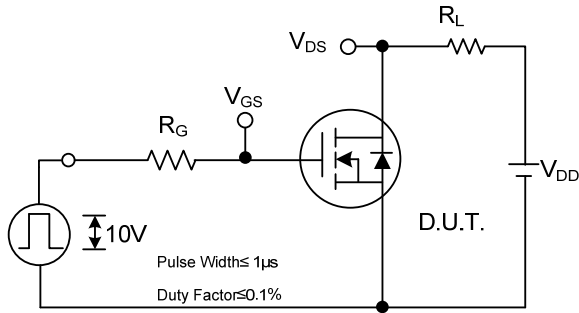


Peak Diode Recovery  $dv/dt$  Test Circuit

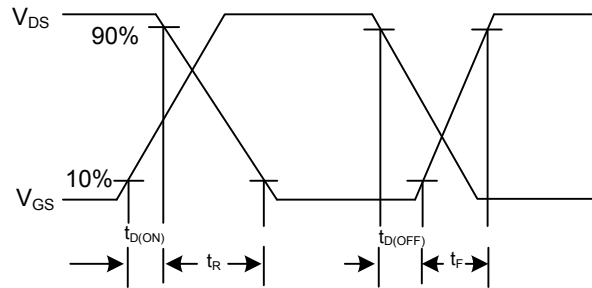


Peak Diode Recovery  $dv/dt$  Waveforms

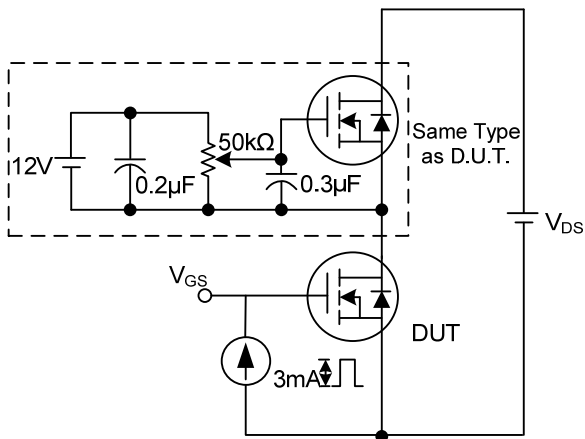
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



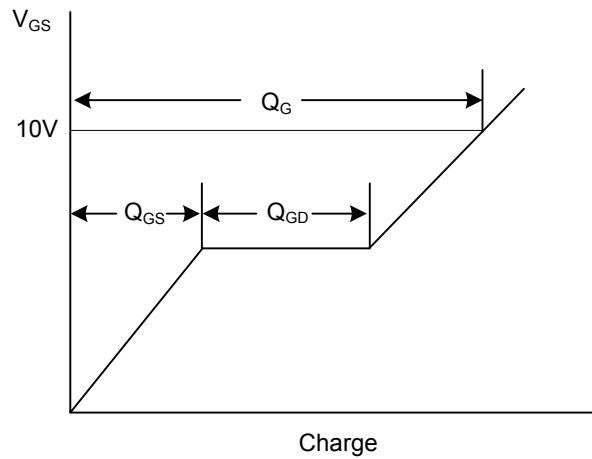
Switching Test Circuit



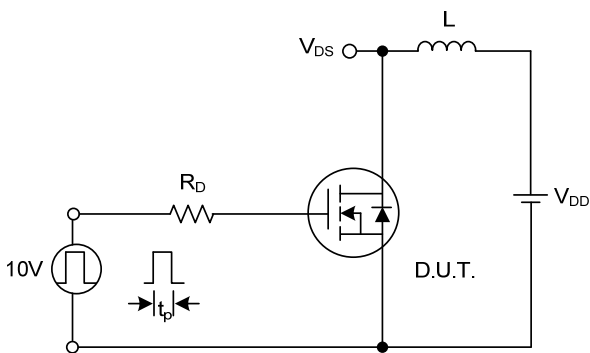
Switching Waveforms



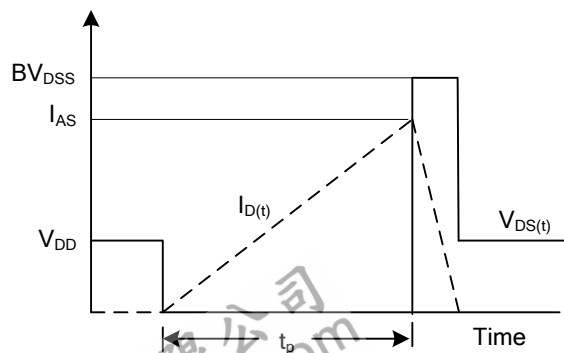
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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